

| | Type | L # | Hits | Search Text | DBs | Tim Stamp |
|---|------|-----|-------|--|--|---------------------|
| 1 | BRS | L27 | 832 | ((lower or source) adj electrode\$3) same (SiN or (Silicon adj nitride) same (TiNiAg) same PSG) | USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B | 2003/08/08 13:40 |
| 2 | BRS | L28 | 284 | ((lower or source) adj electrode\$3) same (SiN or (Silicon adj nitride) same (TiNiAg) same PSG)) and ((upper or top) adj electrode\$3) | USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B | 2003/08/08 13:41 |
| 3 | IS&R | L29 | 1985 | (438/612).CCLS. | USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B | 2003/08/08 13:42 |
| 4 | BRS | L31 | 22347 | 30 and mosfet | USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B | 2003/08/08 13:43 |
| 5 | BRS | L32 | 22356 | 31 "TiNiAg" | USPAT; US-PGP UB; EPO; JPO; DERWENT; IBM_TD B | 2003/08/08 13:44 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
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| 6 | BRS | L33 | 6 | 31 and "TiNiAg" | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 13:46 |
| 7 | BRS | L35 | 13 | 34 and (lift-off or (lift adj3 off) or (lifted adj3 off)) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 14:08 |
| 8 | BRS | L34 | 266 | "bonding pad electrode" | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 14:31 |
| 9 | BRS | L36 | 6838 | "lower electrode" same "upper electrode" same insulat\$4 | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 14:33 |
| 10 | BRS | L37 | 122 | 36 and damascene | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 15:12 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|--|--|---------------------|
| 11 | BRS | L38 | 2 | (upper near2 electrode\$3) near8 TiNiAg | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 15:15 |
| 12 | BRS | L39 | 218 | insulating near8 (SiN or (silicon adj nitride)) near8 (PSG or phospho) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 15:17 |
| 13 | BRS | L40 | 10 | 39 and damascene | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 15:19 |
| 14 | BRS | L41 | 1418 | insulat\$4 same (SiN or (silicon adj nitride)) same (PSG or phospho) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 15:20 |
| 15 | BRS | L42 | 119 | 41 and damascene | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 15:36 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|---|--|---------------------|
| 16 | BRS | L43 | 319 | (lower adj electrode) near4 aluminum | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 15:37 |
| 17 | BRS | L44 | 2 | (upper adj3 electrode) near8 TiNiAg | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 15:38 |
| 18 | BRS | L45 | 283 | insulat\$4 near8 (SiN or "silicon nitride") near8 PSG | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 15:40 |
| 19 | BRS | L46 | 1 | 43 and 45 | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 15:55 |
| 20 | BRS | L47 | 67 | insulating near8 SiN near8 PSG | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 16:02 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|-------|--|--|---------------------|
| 21 | BRS | L48 | 77 | (insulating or insulator) near8 SiN near8 PSG | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 16:02 |
| 22 | BRS | L49 | 10 | 48 not 47 | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 16:05 |
| 23 | BRS | L50 | 3 | electrode near4 TiNiAg | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 16:39 |
| 24 | BRS | L51 | 313 | insulat\$4 same (SiN) same PSG | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 16:39 |
| 25 | BRS | L52 | 25305 | electrode near8 aluminum | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 16:40 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|------|--|--|---------------------|
| 26 | BRS | L56 | 47 | 51 and 52 | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 16:41 |
| 27 | BRS | L54 | 0 | 51 and 52 and 53 | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 17:11 |
| 28 | BRS | L53 | 41 | electrode near8 (TiNiAg or (titanium near2 nickel near2 silver)) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 17:12 |
| 29 | IS&R | L59 | 1985 | (438/612) .CCLS. | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 17:56 |
| 30 | BRS | L60 | 92 | (SiN) near8 PSG near8 (insulating or insulator) | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 17:59 |

| | Type | L # | Hits | Search Text | DBs | Time Stamp |
|----|------|-----|-------|--------------------------|--|---------------------|
| 31 | BRS | L63 | 14416 | electrode near3 aluminum | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 17:59 |
| 32 | BRS | L64 | 12 | 60 and 63 | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 18:17 |
| 33 | IS&R | L67 | 188 | (438/615).CCLS. | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 18:17 |
| 34 | IS&R | L68 | 764 | (257/762).CCLS. | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 18:17 |
| 35 | IS&R | L73 | 1480 | (257/784).CCLS. | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 18:18 |

| | Typ | L # | Hits | Search Text | DBs | Time Stamp |
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| 36 | IS&R | L74 | 1164 | (257/763) .CCLS. | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 18:40 |
| 37 | IS&R | L75 | 584 | (257/766) .CCLS. | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 19:04 |
| 38 | IS&R | L76 | 365 | (257/772) .CCLS. | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 19:11 |
| 39 | IS&R | L77 | 806 | (257/779) .CCLS. | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 19:14 |
| 40 | BRS | L78 | 1775 | bond\$4 near2 pad near2 electrode | USPAT; US-PGP UB; EPO; JPO; DERWEN T; IBM_TD B | 2003/08/08 19:18 |